

BoHS

COMPLIANT HALOGEN

FREE

Vishay Siliconix

P-Channel 20-V (D-S) MOSFET

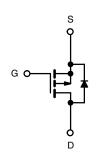
PRODUCT SUMMARY				
V _{DS} (V)	R_{DS(on)} (Ω)	I _D (A)		
- 20	0.019 at V _{GS} = - 4.5 V	- 11.4		
	0.025 at V _{GS} = - 2.5 V	- 9.9		
	0.034 at V _{GS} = - 1.8 V	- 8.5		

FEATURES

- Halogen-free According to IEC 61249-2-21
 Available
- TrenchFET[®] Power MOSFET: 1.8 V Rated
- New PowerPAK[®] Package
- Low Thermal Resistance, $\mathsf{R}_{\mathsf{thJC}}$
- Low 1.07 mm Profile

APPLICATIONS

· Load Switch



P-Channel MOSFET

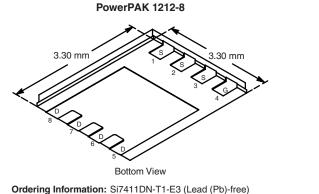
ABSOLUTE MAXIMUM RATINGS $T_A = 25 \text{ °C}$, unless otherwise noted							
Parameter		Symbol	10 s	Steady State	Unit		
Drain-Source Voltage		V _{DS}	- 20		v		
Gate-Source Voltage		V _{GS}	± 8				
Continuous Drain Current (T 150 °C)ª	T _A = 25 °C	– I _D	- 11.4	- 7.5			
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 85 °C		- 8.2	- 5.4	•		
Pulsed Drain Current		I _{DM}	- 30		A		
Continuous Source Current (Diode Conduction) ^a		۱ _S	- 3	- 1.3			
	T _A = 25 °C	P _D	3.6	1.5	W		
Maximum Power Dissipation ^a	T _A = 85 °C		1.9	0.8	vv		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C		
Soldering Recommendations (Peak Temperature) ^{b, c}			260				

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
	t ≤ 10 s	R _{thJA}	28	35		
Maximum Junction-to-Ambient ^a	Steady State		65	81	°C/W	
Maximum Junction-to-Case	Steady State		2.9	3.8		

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

b. See Solder Profile (<u>www.vishay.com/ppg?73257</u>). The PowerPAK 1212-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.



Si7411DN-T1-GE3 (Lead (Pb)-free and Halogen-free)

c. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

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Parameter	Symbol	Test Conditions Min.		Тур.	Max.	Unit	
Static				•			
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = -300 \ \mu A$ - 0.4			- 1.0	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 8 V$			± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = -20 V, V_{GS} = 0 V$		- 1	μA		
		$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 85 ^{\circ}\text{C}$			- 5	μΑ	
On-State Drain Current ^a	I _{D(on)}	$V_{DS}{\leq}$ - 5 V, V_{GS} = - 4.5 V	- 30			А	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 11.4 A		0.015	0.019	Ω	
		V _{GS} = - 2.5 V, I _D = - 9.9 A		0.020	0.025		
		V _{GS} = - 1.8 V, I _D = - 2.9 A 0.027					
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 11.4 A		35		S	
Diode Forward Voltage ^a	V _{SD}	I _S = - 3.0 A, V _{GS} = 0 V		- 0.8	- 1.2	V	
Dynamic ^b							
Total Gate Charge	Qg			27	41		
Gate-Source Charge	Q _{gs}	V_{DS} = - 10 V, V_{GS} = - 4.5 V, I_D = - 11.4 A		3.9		nC	
Gate-Drain Charge	Q _{gd}			7			
Gate Resistance	R _g	f = 1 MHz		5		Ω	
Turn-On Delay Time	t _{d(on)}			23	35		
Rise Time	t _r	V_{DD} = - 10 V, R_L = 10 Ω		45	70		
Turn-Off Delay Time	t _{d(off)}	$\text{I}_\text{D}\cong$ - 1 A, V_GEN = - 4.5 V, R_g = 6 Ω		135	200	ns	
Fall Time	t _f			70	105		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 3.2 A, dl/dt = 100 A/μs		29	50		

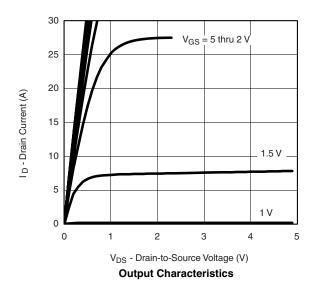
Notes:

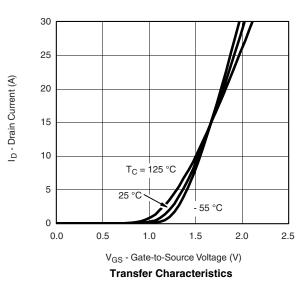
a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

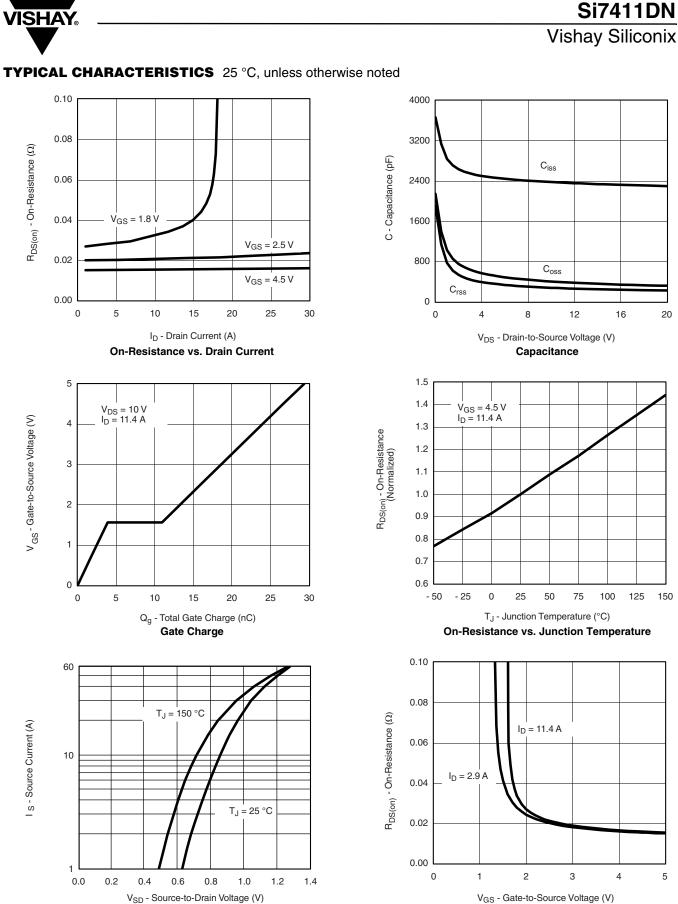
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





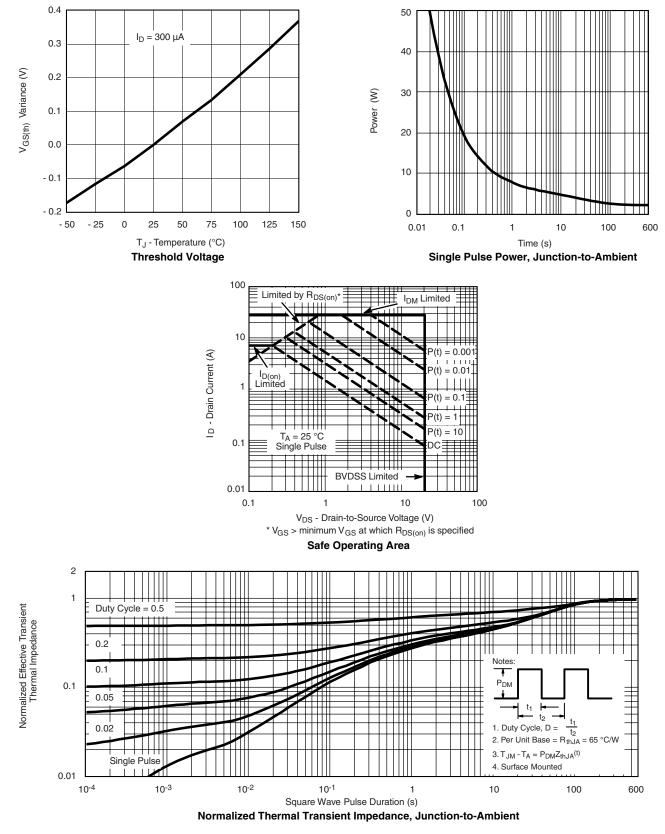


On-Resistance vs. Gate-to-Source Voltage

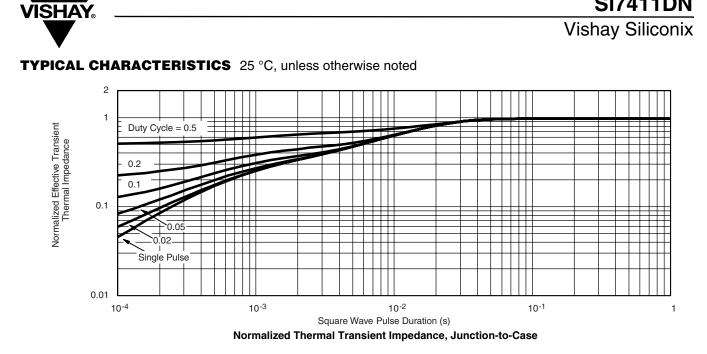
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Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <u>www.vishay.com/ppg?72399</u>.

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